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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	30-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	30-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f103a8dsp-v0

RL78/G12 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

Pin Package Data flash Part Number count Application R5F1026AASP#V5, R5F10269ASP#V5, R5F10268ASP#V5, R5F10267ASP#V5, 20 20-pin plastic Mounted < R> pins LSSOP R5F10266ASP#V5 R5F1026AASP#X5, R5F10269ASP#X5, R5F10268ASP#X5, R5F10267ASP#X5, $(4.4 \times 6.5 \text{ mm},$ 0.65 mm pitch) R5F10266ASP#X5 D R5F1026ADSP#V5, R5F10269DSP#V5, R5F10268DSP#V5, R5F10267DSP#V5, R5F10266DSP#V5 R5F1026ADSP#X5, R5F10269DSP#X5, R5F10268DSP#X5, R5F10267DSP#X5, R5F10266DSP#X5 G R5F1026AGSP#V5, R5F10269GSP#V5, R5F10268GSP#V5, R5F10267GSP#V5, R5F10266GSP#V5 R5F1026AGSP#X5, R5F10269GSP#X5, R5F10268GSP#X5, R5F10267GSP#X5, B5F10266GSP#X5 R5F1036AASP#V5, R5F10369ASP#V5, R5F10368ASP#V5, R5F10367ASP#V5, Not mounted R5F10366ASP#V5 R5F1036AASP#X5, R5F10369ASP#X5, R5F10368ASP#X5, R5F10367ASP#X5, R5F10366ASP#X5 D R5F1036ADSP#V5, R5F10369DSP#V5, R5F10368DSP#V5, R5F10367DSP#V5, R5F10366DSP#V5 R5F1036ADSP#X5, R5F10369DSP#X5, R5F10368DSP#X5, R5F10367DSP#X5, R5F10366DSP#X5 24 24-pin plastic Mounted R5F1027AANA#U5, R5F10279ANA#U5, R5F10278ANA#U5, R5F10277ANA#U5 Α <R> **HWQFN** pins R5F1027AANA#W5, R5F10279ANA#W5, R5F10278ANA#W5, $(4 \times 4 \text{ mm}, 0.5)$ R5F10277ANA#W5 mm pitch) D R5F1027ADNA#U5, R5F10279DNA#U5, R5F10278DNA#U5, R5F10277DNA#U5 R5F1027ADNA#W5, R5F10279DNA#W5, R5F10278DNA#W5, R5F10277DNA#W5 G R5F1027AGNA#U5, R5F10279GNA#U5, R5F10278GNA#U5, R5F10277GNA#U5 R5F1027AGNA#W5, R5F10279GNA#W5, R5F10278GNA#W5, R5F10277GNA#W5 Not mounted Α R5F1037AANA#V5, R5F10379ANA#V5, R5F10378ANA#V5, R5F10377ANA#V5 R5F1037AANA#X5, R5F10379ANA#X5, R5F10378ANA#X5, R5F10377ANA#X5 D R5F1037ADNA#V5, R5F10379DNA#V5, R5F10378DNA#V5, R5F10377DNA#V5 R5F1037ADNA#X5, R5F10379DNA#X5, R5F10378DNA#X5, R5F10377DNA#X5 R5F102AAASP#V0, R5F102A9ASP#V0, R5F102A8ASP#V0, R5F102A7ASP#V0 30 30-pin plastic Mounted Α LSSOP R5F102AAASP#X0, R5F102A9ASP#X0, R5F102A8ASP#X0, R5F102A7ASP#X0 pins (7.62 mm D R5F102AADSP#V0, R5F102A9DSP#V0, R5F102A8DSP#V0, R5F102A7DSP#V0 (300), 0.65 mm R5F102AADSP#X0, R5F102A9DSP#X0, R5F102A8DSP#X0, R5F102A7DSP#X0 pitch) G R5F102AAGSP#V0. R5F102A9GSP#V0. R5F102A8GSP#V0. R5F102A7GSP#V0 R5F102AAGSP#X0, R5F102A9GSP#X0, R5F102A8GSP#X0, R5F102A7GSP#X0 R5F103AAASP#V0, R5F103A9ASP#V0, R5F103A8ASP#V0, R5F103A7ASP#V0 Not mounted Α R5F103AAASP#X0, R5F103A9ASP#X0, R5F103A8ASP#X0, R5F103A7ASP#X0 R5F103AADSP#V0. R5F103A9DSP#V0. R5F103A8DSP#V0. R5F103A7DSP#V0 D R5F103AADSP#X0, R5F103A9DSP#X0, R5F103A8DSP#X0, R5F103A7DSP#X0

Note For fields of application, see Figure 1-1 Part Number, Memory Size, and Package of RL78/G12.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



RL78/G12 1. OUTLINE

1.3 Differences between the R5F102 Products and the R5F103 Products

The following are differences between the R5F102 products and the R5F103 products.

- O Whether the data flash memory is mounted or not
- O High-speed on-chip oscillator oscillation frequency accuracy
- O Number of channels in serial interface
- O Whether the DMA function is mounted or not
- O Whether a part of the safety functions are mounted or not

1.3.1 Data Flash

The data flash memory of 2 KB is mounted on the R5F102 products, but not on the R5F103 products.

Product	Data Flash
R5F102 products	2KB
R5F1026A, R5F1027A, R5F102AA,	
R5F10269, R5F10279, R5F102A9,	
R5F10268, R5F10278, R5F102A8,	
R5F10267, R5F10277, R5F102A7,	
R5F10266 Note	
R5F103 products	Not mounted
R5F1036A, R5F1037A, R5F103AA,	
R5F10369, R5F10379, R5F103A9,	
R5F10368, R5F10378 R5F103A8,	
R5F10367, R5F10377, R5F103A7,	
R5F10366	

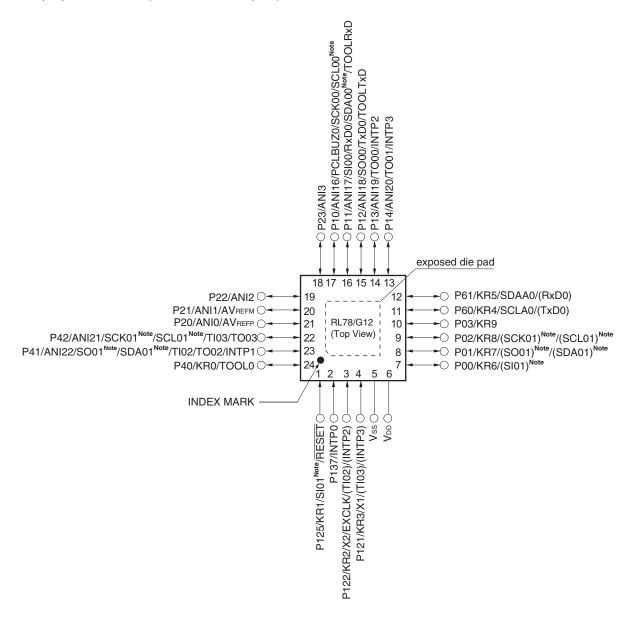
Note The RAM in the R5F10266 has capacity as small as 256 bytes. Depending on the customer's program specification, the stack area to execute the data flash library may not be kept and data may not be written to or erased from the data flash memory.

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

RL78/G12 1. OUTLINE

1.4.2 24-pin products

<R> • 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see 1.5 Pin Identification.

- 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR).
- 3. It is recommended to connect an exposed die pad to Vss.

(2) 30-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

			3 0.0 V, V33 =	/						(1/2
Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (High-speed	f _{IH} = 24 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		1.5		mA
current Note 1		mode	main) mode Note 4		operation	V _{DD} = 3.0 V		1.5		
					Normal	V _{DD} = 5.0 V		3.7	5.5	mA
					operation	V _{DD} = 3.0 V		3.7	5.5	
				f _{IH} = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.7	4.0	mA
					V _{DD} = 3.0 V		2.7	4.0		
			LS (Low-speed	f _{IH} = 8 MHz ^{Note 3}		V _{DD} = 3.0 V		1.2	1.8	mA
main) mode	main) mode Note 4			V _{DD} = 2.0 V		1.2	1.8			
			,			Square wave input		3.0	4.6	mA
	main) mode Note 4	$V_{DD} = 5.0 \text{ V}$		Resonator connection		3.2	4.8			
			<u> </u>	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		3.0	4.6	mA
				V _{DD} = 3.0 V		Resonator connection		3.2	4.8	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$		Square wave input		1.9	2.7	mA
				$V_{DD} = 5.0 \text{ V}$		Resonator connection		1.9	2.7	
				$f_{MX} = 10 \text{ MHz}^{Note 2}$		Square wave input		1.9	2.7	mA
				V _{DD} = 3.0 V		Resonator connection		1.9	2.7	
			LS (Low-speed	$f_{MX} = 8 MHz^{Note 2}$		Square wave input		1.1	1.7	mA
	main) mode Note 4	main) mode Note 4	$V_{DD} = 3.0 \text{ V}$		Resonator connection		1.1	1.7		
				$f_{MX} = 8 MHz^{Note 2}$		Square wave input		1.1	1.7	mA
				$V_{DD} = 2.0 \text{ V}$		Resonator connection		1.1	1.7	

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator clock is stopped.
 - 3. When high-speed system clock is stopped
 - **4.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: VDD = 2.7 V to 5.5 V @ 1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS(Low speed main) mode: $V_{DD} = 1.8 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 8 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25$ °C.

2.4 AC Characteristics

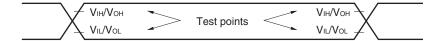
$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol		Condition	S	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Tcy	Main system	HS (High-	$2.7~V \leq V_{DD} \leq 5.5~V$	0.04167		1	μS
instruction execution time)		clock (fMAIN) operation	speed main) mode	$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$	0.0625		1	μS
			LS (Low- speed main) mode	$1.8~V \leq V_{DD} \leq 5.5~V$	0.125		1	μs
		During self	HS (High-	$2.7~V \leq V_{DD} \leq 5.5~V$	0.04167		1	μS
		programming	speed main) mode	$2.4~V \leq V_{DD} < 2.7~V$	0.0625		1	μS
			LS (Low- speed main) mode	$1.8~V \le V_{DD} \le 5.5~V$	0.125		1	μs
External main system clock	fex	$2.7~V \leq V_{DD} \leq 5$	1.0		20.0	MHz		
frequency		$2.4~V \leq V_{DD} < 2.7~V$			1.0		16.0	MHz
		$1.8~V \leq V_{DD} < 2$.4 V		1.0		8.0	MHz
External main system clock	texh, texl	H, texl $2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$						ns
input high-level width, low-level width		$2.4~V \leq V_{DD} < 2.7~V$			30			ns
level width		$1.8~V \leq V_{DD} < 2$	60			ns		
TI00 to TI07 input high-level width, low-level width	тпн, тп∟				1/fмск + 10			ns
TO00 to TO07 output	fто	4.0 V ≤ V _{DD} ≤ 5	.5 V				12	MHz
frequency		$2.7~V \leq V_{DD} < 4$.0 V				8	MHz
		1.8 V ≤ V _{DD} < 2.7 V					4	MHz
PCLBUZ0, or PCLBUZ1	f PCL	4.0 V ≤ V _{DD} ≤ 5	.5 V				16	MHz
output frequency		$2.7~V \leq V_{DD} < 4$.0 V				8	MHz
		1.8 V ≤ V _{DD} < 2	.7 V				4	MHz
INTP0 to INTP5 input high- level width, low-level width	tinth, tintl				1			μS
KR0 to KR9 input available width	tĸĸ				250			ns
RESET low-level width	trsl				10			μS

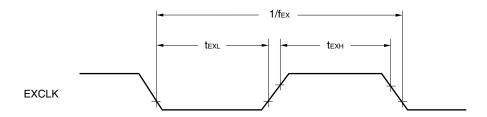
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0 (TMR0n). n: Channel number (n = 0 to 7))

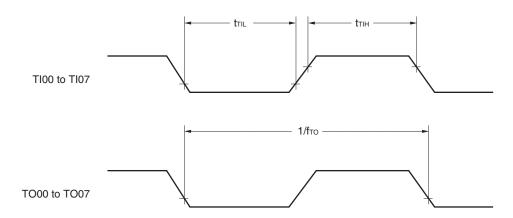
AC Timing Test Point



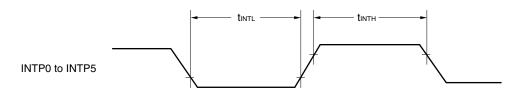
External Main System Clock Timing



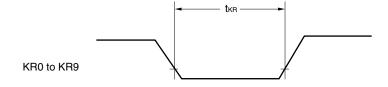
TI/TO Timing



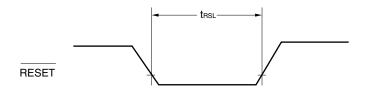
Interrupt Request Input Timing



Key Interrupt Input Timing



RESET Input Timing



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) ($T_A = -40$ to +85°C, 1.8 V \leq V_{DD} \leq 5.5 V, Vss = 0 V)

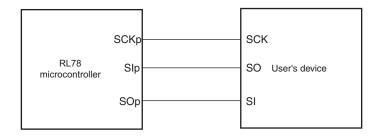
Parameter	Symbol	C	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode	
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fcLk	$2.7~V \leq V_{DD} \leq 5.5~V$	167		500		ns
			$2.4~V \leq V_{DD} \leq 5.5~V$	250		500		ns
			$1.8~V \leq V_{DD} \leq 5.5~V$	-		500		ns
SCKp high-/low-level width	tкн1,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$ th		tксү1/2-12		tkcy1/2-50		ns
	t _{KL1}	$2.7~V \leq V_{DD} \leq 5.5~V$		tkcy1/2-18		tkcy1/2-50		ns
		$2.4~V \leq V_{DD} \leq 5.5~V$		tkcy1/2-38		tkcy1/2-50		ns
		$1.8~V \leq V_{\text{DD}} \leq 5.5~V$		-		tkcy1/2-50		ns
SIp setup time (to SCKp↑)	tsıĸı	$4.0~V \leq V_{DD} \leq 5.5~V$		44		110		ns
Note 1		$2.7~V \leq V_{DD} \leq 5.5~V$		44		110		ns
		$2.4~V \leq V_{DD} \leq$	$2.4~V \leq V_{DD} \leq 5.5~V$			110		ns
		$1.8~V \leq V_{DD} \leq$	5.5 V	-		110		ns
SIp hold time (from SCKp↑) Note 2	tksıı			19		19		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note4			25		25	ns

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp \uparrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

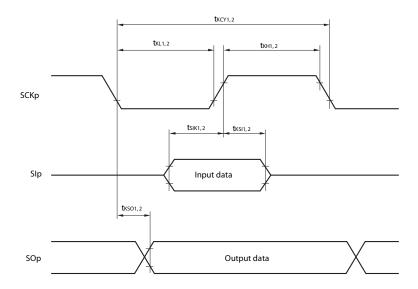
Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

- **Remarks 1.** p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products)
 - 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.))

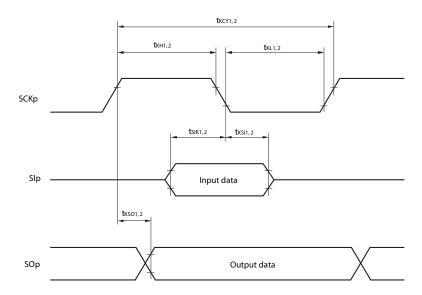
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

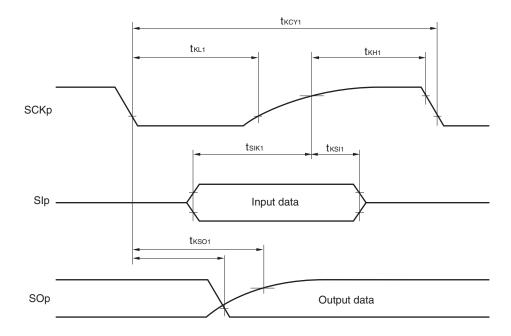


(Remarks are listed on the next page.)

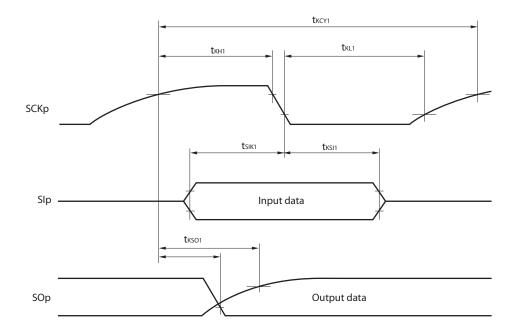
- Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1
 - **2.** When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
- Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (VDD tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

 For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** Rb [Ω]:Communication line (SCK00, SO00) pull-up resistance, Cb [F]: Communication line (SCK00, SO00) load capacitance, Vb [V]: Communication line voltage
 - fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel		Reference Voltage							
	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = Vss	Reference voltage (+) = VBGR Reference voltage (-) = AVREFM						
ANI0 to ANI3	Refer to 28.6.1 (1).	Refer to 28.6.1 (3).	Refer to 28.6.1 (4).						
ANI16 to ANI22	Refer to 28.6.1 (2).								
Internal reference voltage	Refer to 28.6.1 (1).		-						
Temperature sensor output voltage									

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.8 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	10-bit resolution		1.2	±3.5	LSB
		AVREFP = VDD Note 3			1.2	±7.0 Note 4	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2, ANI3	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
				57		95	μS
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
		output voltage (HS (high-speed main) mode)					
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution				±0.25	%FSR
		AVREFP = VDD Note 3				$\pm 0.50^{\text{Note 4}}$	%FSR
Full-scale errorNotes 1, 2	EFS	10-bit resolution				±0.25	%FSR
		AVREFP = VDD Note 3	$AV_{REFP} = V_{DD}^{Note 3}$			$\pm 0.50^{\text{Note 4}}$	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±2.5	LSB
		AVREFP = VDD Note 3				±5.0 Note 4	LSB
Differential linearity error	DLE	10-bit resolution				±1.5	LSB
Note 1		AVREFP = VDD Note 3				±2.0 Note 4	LSB
Analog input voltage	VAIN	ANI2, ANI3		0		AVREFP	V
		Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS	V _{BGR} Note 5			V	
		Temperature sensor outp (2.4 V \leq VDD \leq 5.5 V, HS	V _{TMPS25} Note 5			V	

(Notes are listed on the next page.)



2.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = -40 to +85°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode

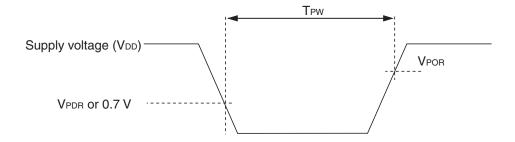
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	FVTMPS	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tамр		5			μS

2.6.3 POR circuit characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

<u>, </u>						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Vpor	Power supply rise time	1.47	1.51	1.55	٧
	V _{PDR}	Power supply fall time	1.46	1.50	1.54	٧
Minimum pulse width Note	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{PDR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



LVD detection voltage of interrupt & reset mode

(T_A = -40 to +85°C, V_{PDR} \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol		Con	MIN.	TYP.	MAX.	Unit	
Interrupt and reset	V _{LVDB0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 0, 1, fa	1.80	1.84	1.87	V	
mode	V _{LVDB1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V _{LVDB2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V _{LVDB3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V _{LVDC0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 1, 0, fa	lling reset voltage	2.40	2.45	2.50	V
	V _{LVDC1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	V _{LVDC2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V _{LVDC3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V _{LVDD0}	V _{POC2} ,	VPOC1, VPOC1 = 0, 1, 1, fa	lling reset voltage	2.70	2.75	2.81	V
	V _{LVDD1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	V _{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

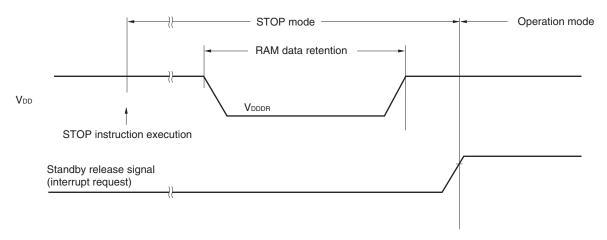
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 28.4 AC Characteristics.

<R> 2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

, , , , , , , , , , , , , , , , , , , ,						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V _{DDDR}		1.46 Note		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

$(1A = -40 \text{ to } +65 \text{ C}, 1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{ VSS} = 0 \text{ V})$							
<r> Parameter</r>	Parameter S		Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	1	fclk		1		24	MHz
Code flash memory rewrita	able times	Cerwr	Retained for 20 years	1,000			Times
Notes 1, 2, 3			T _A = 85°C				
Data flash memory rewrita	ble times		Retained for 1 year		1,000,000		
Notes 1, 2, 3			T _A = 25°C				
			Retained for 5 years	100,000			
			$T_A = 85^{\circ}C$				
			Retained for 20 years	10,000			
			T _A = 85°C				

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(3/4)

Parameter	Symbol	Condition	S	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Normal input buffer		0.8V _{DD}		V_{DD}	V
		20-, 24-pin products: P00 to P0 P40 to P42					
		30-pin products: P00, P01, P1 P40, P50, P51, P120, P147	0 to P17, P30, P31,				
	V _{IH2}	TTL input buffer	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	2.2		V _{DD}	٧
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		V _{DD}	٧
		30-pin products: P01, P10, P11, P13 to P17	2.4 V ≤ V _{DD} < 3.3 V	1.5		V _{DD}	V
	VIH3	Normal input buffer P20 to P23		V _{DD}	V		
	V _{IH4}	P60, P61		0.7V _{DD}		6.0	V
	V _{IH5}	P121, P122, P125 ^{Note 1} , P137, I	0.8V _{DD}		V_{DD}	٧	
Input voltage, low	V _{IL1}	Normal input buffer		0	0		V
		20-, 24-pin products: P00 to P0 P40 to P42	03 ^{Note 2} , P10 to P14,				
		30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147					
	V _{IL2}	TTL input buffer	$4.0~V \leq V_{DD} \leq 5.5~V$	0		0.8	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	٧
		30-pin products: P01, P10, P11, P13 to P17	2.4 V ≤ V _{DD} < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P23		0		0.3V _{DD}	٧
	V _{IL4}	P60, P61		0		0.3V _{DD}	٧
	V _{IL5}	P121, P122, P125 ^{Note 1} , P137, I	EXCLK, RESET	0		0.2V _{DD}	V
Output voltage, high	V _{OH1}	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	V _{DD} -0.7			V
		P40 to P42 30-pin products:	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -2.0 \text{ mA}$	V _{DD} -0.6			V
		P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.5 \text{ mA}$	V _{DD} -0.5			V
	V _{OH2}	P20 to P23	Іон2 = -100 μΑ	V _{DD} -0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) 30-pin products

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit									
Supply	I _{DD1}	Operating	HS (High-speed	f _{IH} = 24 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		1.5		mA									
current ^{Note 1}		mode	main) mode Note 4		operation	V _{DD} = 3.0 V		1.5											
					Normal	V _{DD} = 5.0 V		3.7	5.8	mA									
					operation	V _{DD} = 3.0 V		3.7	5.8										
				f _{IH} = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.7	4.2	mA									
									V _{DD} = 3.0 V		2.7	4.2							
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		3.0	4.9	mA									
					$V_{DD} = 5.0 \text{ V}$		Resonator connection		3.2	5.0									
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		3.0	4.9	mA									
												V _{DD} = 3.0 V	$V_{DD} = 3.0 \text{ V}$	Resonato	Resonator connection		3.2	5.0	
				$f_{MX} = 10 \text{ MHz}^{Note 2},$		Square wave input		1.9	2.9	mA									
			VD	$V_{DD} = 5.0 \text{ V}$		Resonator connection		1.9	2.9										
				$f_{MX} = 10 \text{ MHz}^{Note 2},$		Square wave input		1.9	2.9	mA									
				$V_{DD} = 3.0 \text{ V}$		Resonator connection		1.9	2.9										

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator clock is stopped.
 - 3. When high-speed system clock is stopped
 - **4.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: $V_{DD} = 2.7 \text{ V to } 5.5 \text{ V} @ 1 \text{ MHz to } 24 \text{ MHz}$ $V_{DD} = 2.4 \text{ V to } 5.5 \text{ V} @ 1 \text{ MHz to } 16 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$.

(3) Peripheral functions (Common to all products)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	IFIL Note 1				0.20		μΑ
12-bit interval timer operating current	ITMKA Notes 1, 2, 3				0.02		μΑ
Watchdog timer operating current	WDT Notes 1, 2, 4	fı∟ = 15 kHz	L = 15 kHz				μΑ
A/D converter	IADC	When conversion	Normal mode, AVREFP = VDD = 5.0 V		1.30	1.70	mA
operating current Notes 1, 5	Notes 1, 5	at maximum speed	Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	ADREF Note 1				75.0		μΑ
Temperature sensor operating current	ITMPS Note 1				75.0		μА
LVD operating current	ILVD Notes 1, 6				0.08		μΑ
Self-programming operating current	FSP Notes 1, 8				2.00	12.20	mA
BGO operating current	BGO Notes 1, 7				2.00	12.20	mA
SNOOZE operating	Isnoz	ADC operation	The mode is performed Note 9		0.50	1.10	mA
current	Note 1		The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	2.04	mA
		CSI/UART operation	1		0.70	1.54	mA

Notes 1. Current flowing to the VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IFIL and ITMKA when the 12-bit interval timer operates.
- 4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
- **5.** Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **6.** Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit operates.
- 7. Current flowing only during data flash rewrite.
- 8. Current flowing only during self programming.
- 9. For shift time to the SNOOZE mode, see 17.3.3 SNOOZE mode.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

2. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		bit
Conversion time	tconv	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		V _{BGR} Note 3	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 29.6.2 Temperature sensor/internal reference voltage characteristics.
 - **4.** When reference voltage (–) = Vss, the MAX. values are as follows. Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (–) = AV_{REFM}.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AVREFM.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.9 Dedicated Flash Memory Programmer Communication (UART)

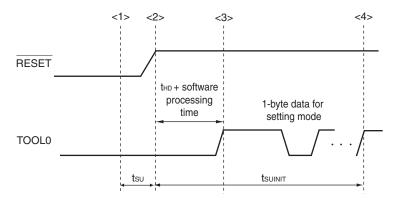
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

1 11 1, = = 1 1,	·· ,					
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset are released before external release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset are released before external release	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released	thd	POR and LVD reset are released before external release	1			ms
(excluding the processing time of the firmware to control the flash memory)						



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



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